

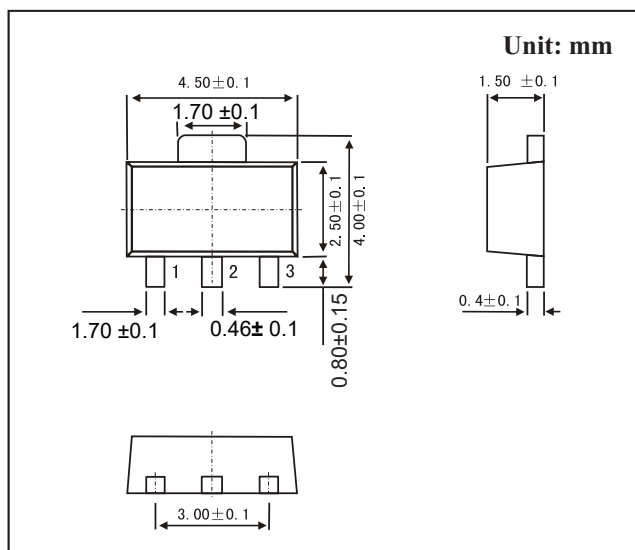
SOT-89 Plastic-Encapsulate Transistors

FEATURES

- High V_{CEO} , $V_{CEO}=80V$
- High I_C , $I_C=1A$ (DC)
- Low $V_{CE(sat)}$
- Complementary to 2SB1260
- NPN Transistors

MECHANICAL DATA

- Case style:SOT-89 molded plastic
- Mounting position:any



MAXIMUM RATINGS AND CHARACTERISTICS

@ 25°C Ambient Temperature (unless otherwise noted)

Parameter	Symbol	Rating	Unit
Collector - Base Voltage	V_{CBO}	120	V
Collector - Emitter Voltage	V_{CEO}	80	
Emitter - Base Voltage	V_{EBO}	5	
Collector Current - Continuous	I_C	1	A
Collector Current - Pulse	I_{CP}	2	
Collector Power Dissipation	P_C	0.5	W
		2	
Junction Temperature	T_J	150	°C
Storage Temperature Range	T_{stg}	-55 to +150	

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector- base breakdown voltage	V_{CBO}	$I_C = 100 \mu A$, $I_E = 0$	120			V
Collector- emitter breakdown voltage	V_{CEO}	$I_C = 1 mA$, $I_B = 0$	80			
Emitter - base breakdown voltage	V_{EBO}	$I_E = 100 \mu A$, $I_C = 0$	5			
Collector-base cut-off current	I_{CBO}	$V_{CB} = 100 V$, $I_E = 0$			1	μA
Emitter cut-off current	I_{EBO}	$V_{EB} = 4 V$, $I_C = 0$			0.5	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = 500 mA$, $I_B = 50 mA$		0.15	0.4	V
Base - emitter saturation voltage	$V_{BE(sat)}$	$I_C = 500 mA$, $I_B = 50 mA$			1.2	
DC current gain	h_{FE}	$V_{CE} = 3 V$, $I_C = 500 mA$	120		390	
Collector Output capacitance	C_{ob}	$V_{CB} = 10 V$, $I_E = 0$, $f = 1 MHz$		20		pF
Transition frequency	f_T	$V_{CE} = 10 V$, $I_E = -50 mA$, $f = 100 MHz$		100		MHz

RATINGS AND CHARACTERISTIC CURVES

